TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS III)

2SK4033

Chopper Regulator, DC/DC Converter and Motor Drive Applications

4 V gate drive

• Low drain–source ON-resistance : $R_{DS\ (ON)} = 0.07\ \Omega$ (typ.) • High forward transfer admittance : $|Y_{fs}| = 6.0\ S$ (typ.) • Low leakage current : $I_{DSS} = 100\ \mu\text{A}$ (max) ($V_{DS} = 60\ V$) • Enhancement mode : $V_{th} = 0.8 \sim 2.0\ V$ ($V_{DS} = 10\ V$, $I_{D} = 1\ m\text{A}$)

Maximum Ratings (Ta = 25°C)

Character	istic	Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	60	V
Drain-gate voltage (R	_{GS} = 20 kΩ)	V_{DGR}	60	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I _D	5	Α
Diam current	Pulse (Note 1)	I_{DP}	20	Α
Drain power dissipation	n (Tc = 25°C)	P_{D}	20	W
Single-pulse avalanch	e energy (Note 2)	E _{AS}	40.5	mJ
Avalanche current		I _{AR}	5	Α
Repetitive avalanche	energy (Note 3)	E _{AR}	2	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature r	ange	T _{stg}	-55~150	°C

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	6.25	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	125	°C/W

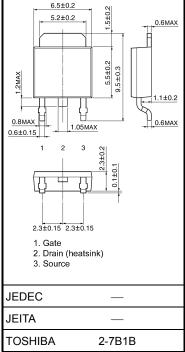
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 2.2 mH, R_G = 25 Ω , I_{AR} = 5 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.36 g (typ.)

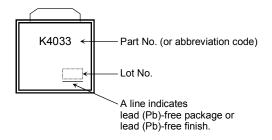
Electrical Characteristics (Ta = 25°C)

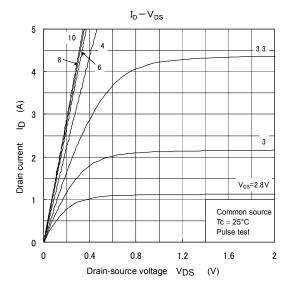
Chara	cteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μА
Drain cutoff curr	ent	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	_	_	100	μА
Drain-source br	reakdown	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	60	_	_	٧
Gate threshold	/oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3	_	2.5	V
Drain-source ON-resistance		В	V _{GS} = 4 V, I _D = 2.5 A	_	0.09	0.15	
		R _{DS} (ON)	V _{GS} = 10 V, I _D = 2.5 A	_	0.07	0.10	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 2.5 A	3.0	6.0	_	S
Input capacitano	ce	C _{iss}		_	730	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	60	_	pF
Output capacitance		Coss		_	95	_	
Switching time	Rise time	t _r	$V_{\text{CS}} = \frac{10\text{V}}{0\text{V}} = \frac{I_{\text{D}} = 2.5\text{A}}{\text{V}_{\text{OUT}}} = \frac{10\text{V}}{0\text{V}_{\text{DO}}} = 30\text{V}$ $V_{\text{DO}} = 30\text{V}$ $\text{Duty} \le 1\%, t_{\text{W}} = 10 \mu\text{s}$	_	10	_	
	Turn-on time	t _{on}		_	20	_	ns
	Fall time	t _f		_	4	_	115
	Turn-off time	t _{off}		_	35	_	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 48 V, V _{GS} = 10 V, I _D = 5 A		15		_
Gate-source charge		Q _{gs}		_	11		nC
Gate-drain ("Miller") charge		Q _{gd}		_	4	_	

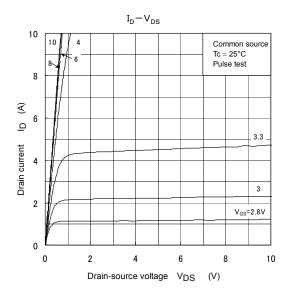
Source-Drain Ratings and Characteristics (Ta = 25°C)

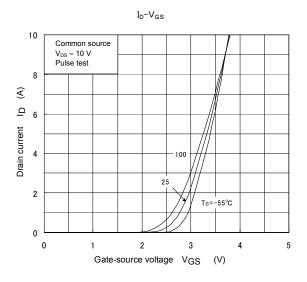
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	5	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	20	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 5 A, V _{GS} = 0 V, dI _{DR} / dt = 50 A / μs	_	34	_	ns
Reverse recovery charge	Q _{rr}	1DR = 3 A, VGS = 0 V, αDR / αt = 30 A / μs	_	28	_	μС

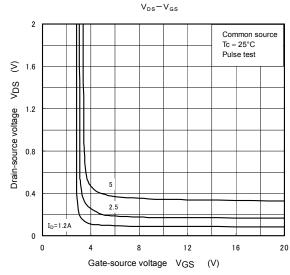
Marking

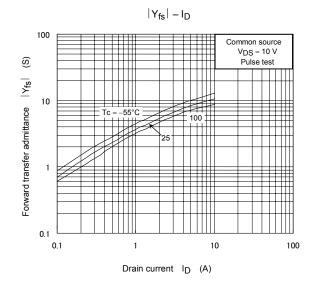


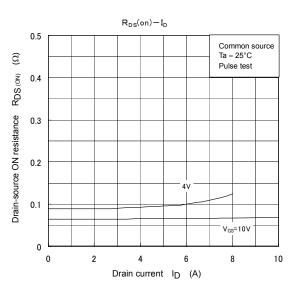


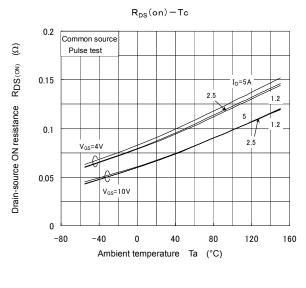


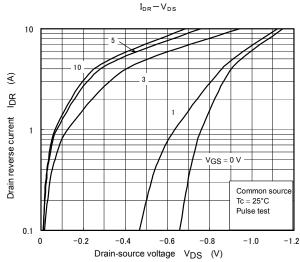


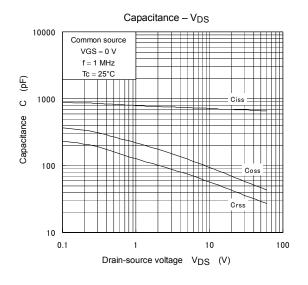


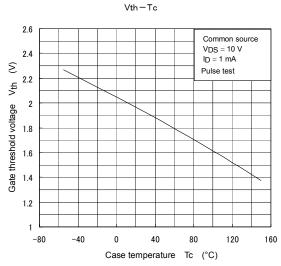


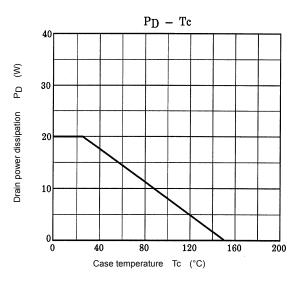


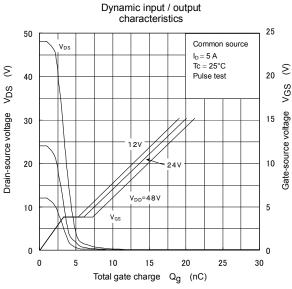


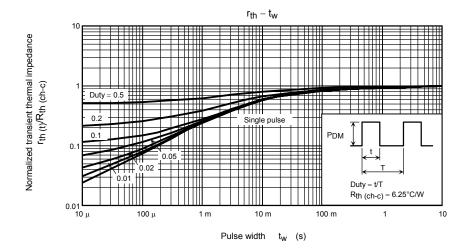




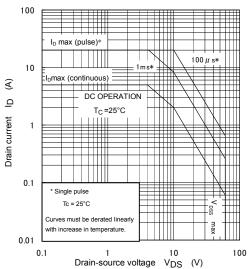


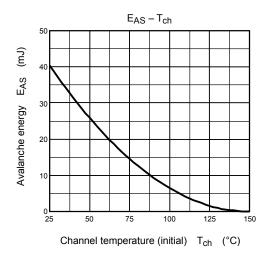


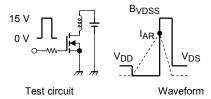












$$\begin{aligned} R_G &= 25~\Omega \\ V_{DD} &= 25~V,~L = 2.2~mH \end{aligned}$$

$$\mathsf{E}_{AS} = \frac{1}{2} \cdot L \cdot l^2 \cdot \left(\frac{\mathsf{BVDSS}}{\mathsf{BVDSS} - \mathsf{VDD}} \right)$$

RESTRICTIONS ON PRODUCT USE

060116EAA

- The information contained herein is subject to change without notice. 021023_D
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc. 021023_A
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk. 021023_B
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations. 060106_Q
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
 may result from its use. No license is granted by implication or otherwise under any patent or patent rights of
 TOSHIBA or others. 021023 c